

13-16, 21, and 33 have been amended, and new claims 57-65 have been added. Accordingly, claims 9-12, 13-16, 21-24, 33-36, 50-52, 54, and 57-65 are pending in the present application, of which claims 9, 13, 21, 33, 57-59 are independent.

Referring now to the Office Action, claims 9-16, 21-24, 33-40, 45-48, 50-52, and 54-56 are rejected under 35 U.S.C. § 103(a) as allegedly unpatentable over Inaba et al. (U.S. Patent No. 5,227,900) in view of Takeshita et al. (JP 61-141174). The rejection is respectfully traversed at least for the reasons provided below.

Claims 37-40, 45-48, 55, and 56, which recited reciting a projector, have been canceled. Accordingly, the § 103(a) rejection of claims 37-40, 45-48, 55, and 56 is now moot.

Claims 9, 13-16, 21, and 33 have been amended to delete the limitations of the leveling film provided over the second (opposed) substrate.

New claims 57-65 do not include a feature of organic resin constituting the leveling film covering a TFT or a semiconductor element.

As previously submitted in Applicants' Response, dated March 13, 2001, Inaba et al. and Takeshita et al. fail to appreciate the problem caused by the narrow cell gap of the FLC/AFLC display device, and the materiality of the flatness of the inside surface of the substrate in the FLC/AFLC display. As such, neither of the cited prior art references teach, disclose or suggest the claimed invention. Therefore, the combination of Inaba et al. and Takeshita et al. is insupportable.

In view of the amendments and arguments set forth above, the § 103(a) rejection is respectfully requested to be reconsidered and withdrawn.

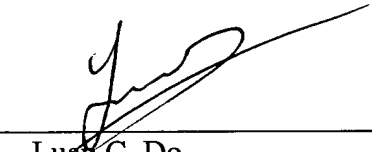
CONCLUSION

Having responded to all rejections set forth in the outstanding non-Final Office Action, it is submitted that claims 9-12, 13-16, 21-24, 33-36, 50-52, 54, and 57-65 are now in condition for allowance. An early and favorable Notice of Allowance is respectfully solicited. In the event that the Examiner is of the opinion that a brief telephone or personal interview will facilitate allowance of one or more of the above claims, the Examiner is courteously requested to contact Applicants' undersigned representative.

Application No.: 09/352,194
Art Unit: 2823

Attorney Docket No.: 740756-1998
Page 9

Respectfully submitted,

By 
Luan C. Do
Reg. No. 38,434

NIXON PEABODY, LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
Telephone: (703) 790-9110
Facsimile: (703) 883-0370

VERSION OF AMENDED CLAIM WITH
MARKINGS TO SHOW CHANGES MADE

9. (Twice amended) A device having at least one liquid crystal panel, said liquid crystal panel comprising:

a first substrate having an insulating surface;

a second substrate being opposed to the first substrate;

at least one thin film transistor being formed over the first substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

wherein the channel region, the source and drain region of said one thin film transistor is formed in a semiconductor island;

an organic resin film formed over said first substrate to provide a leveled upper surface over said first substrate, said organic resin film covering said thin film transistor;

a pixel electrode formed on said leveled upper surface, said pixel electrode being electrically connected to said thin film transistor through an opening formed in said organic resin film;

a liquid crystal material having ferroelectricity or anti-ferroelectricity and being formed between the first substrate and the second substrate;

[a leveling film being formed over said second substrate;]

an opposed electrode formed over said [leveling film] second substrate and opposed to said pixel electrode with said liquid crystal material interposed therebetween.

13. (Thrice amended) A device having at least one liquid crystal panel, said liquid crystal panel comprising:

a first substrate having an insulating surface;

a second substrate being opposed to the first substrate;

at least one semiconductor element being formed over the first substrate, said semiconductor element including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

wherein the channel region, the source and drain region of said one semiconductor element is formed in a semiconductor island;

an organic resin film formed over said first substrate to provide a leveled upper surface over said first substrate, said organic resin film covering said semiconductor element;

a pixel electrode formed on said leveled upper surface, said pixel electrode being electrically connected to said semiconductor element through an opening formed in said organic resin film;

a liquid crystal material having ferroelectricity or anti-ferroelectricity and being formed between the first substrate and the second substrate, and

[a leveling film being formed over said second substrate;]

an opposed electrode formed over said [leveling film] second substrate and opposed to said pixel electrode with said liquid crystal material interposed therebetween.

14. (Amended) A [television] device according to claim 13, wherein said organic resin film comprises polyimide.

15. (Amended) A [television] device according to claim 13, wherein said pixel electrode is transparent.

16. (Amended) A [television] device according to claim 13, wherein said thin film transistor is a top-gate type in which said gate electrode is located above said channel region.

21. (Twice amended) A television comprising:

a tuner for receiving television radio wave;

a liquid crystal panel operationally connected to said tuner, said liquid crystal panel comprising:

a first substrate having an insulating surface;

a second substrate being opposed to the first substrate;

at least one thin film transistor being formed over the first substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

wherein the channel region, the source and drain region of said one thin film transistor is formed in a semiconductor island;

an organic resin film formed over said first substrate to provide a leveled upper surface over said first substrate, said organic resin film covering said thin film transistor;

a pixel electrode formed on said leveled upper surface, said pixel electrode being electrically connected to said thin film transistor through an opening formed in said organic resin film;

a liquid crystal material having ferroelectricity or anti-ferroelectricity and being formed between the first substrate and the second substrate;

[a leveling film being formed over said second substrate;]

an opposed electrode formed over said [leveling film] second substrate and opposed to said pixel electrode with said liquid crystal material interposed therebetween.

33. (Twice amended) A portable computer having a liquid crystal panel, said liquid crystal panel comprising:

a first substrate having an insulating surface;

a second substrate being opposed to the first substrate;

at least one thin film transistor being formed over the first substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

wherein the channel region, the source and drain region of said one thin film transistor is formed in a semiconductor island;

an organic resin film formed over said first substrate to provide a leveled upper surface over said first substrate, said organic resin film covering said thin film transistor;

a pixel electrode formed on said leveled upper surface, said pixel electrode being electrically connected to said thin film transistor through an opening formed in said organic resin film;

a liquid crystal material having ferroelectricity or anti-ferroelectricity and being formed between the first substrate and the second substrate;

[a leveling film being formed over said second substrate;]

an opposed electrode formed over said [leveling film] second substrate and opposed to said pixel electrode with said liquid crystal material interposed therebetween.